Performance

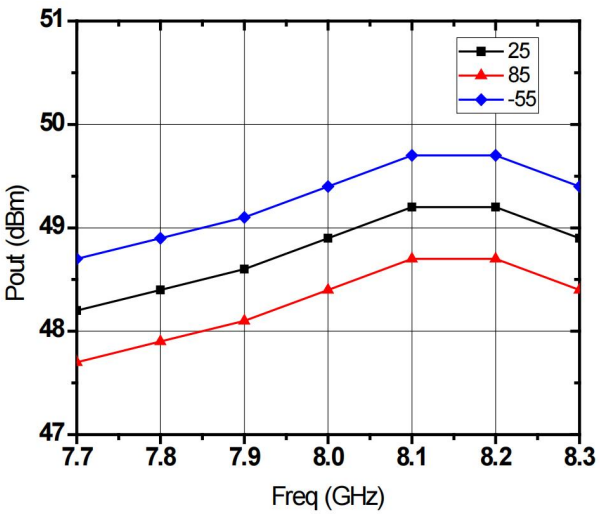
- Technology: 0.25um Power GaN HEMT
- Frequency: 7.7~8.5GHz
- Typical Pout : 48dBm(CW)
- Typical Gain: 8dB
- Typical PAE: 45%
- Bias: 28V/-2~-3V
- Package: Metal Ceramic

Electrical Specifications (T_A=25℃,V_d=28V,Vg=-2~-3V,Id≈8A,F: 7.7~8.5GHz)

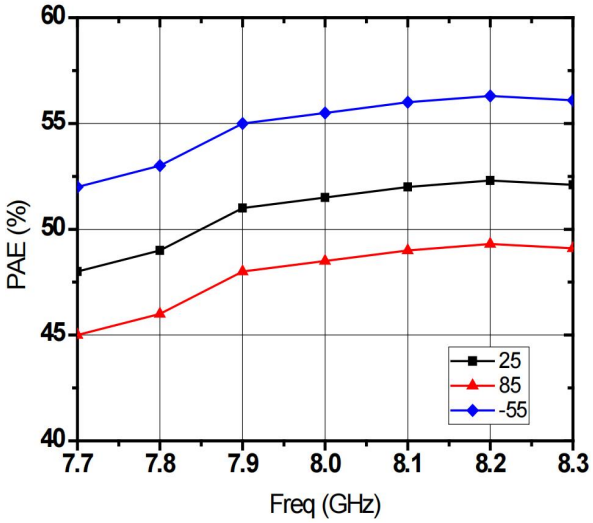
Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	-	48	-	dBm
Gp	Power Gain	-	8	-	dB
ηadd	Power Added Efficiency	-	45	-	%
Rth	Thermal Resistance	-	-	-	℃/W
△Gp	Gain Flatness	-0.8	-	+0.8	dB

Test Curves

Pout&Freq. @ Different Temp.



PAE&Freq. @ Different Temp.

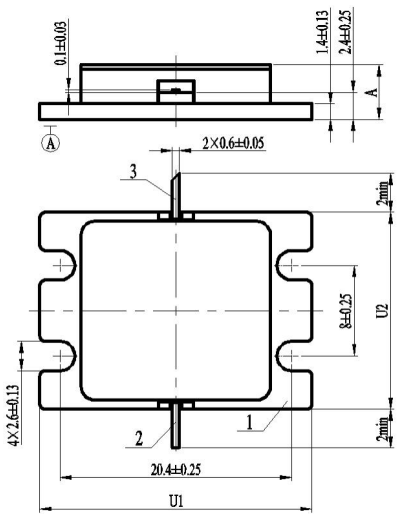


Absolute Max Ratings (T_A=25℃)

Symbol	Parameter	Value	Remark
Vd	Drain Voltage	40V	
Vg	Grid Voltage	-5V	
Pd	DC Dissipation	100W	25℃
Tch	Channel Temperature	225℃	【1】
Tm	Mounting Temperature	300℃	1 min, N_2 Protection
Tstg	Storage Temperature	-55~175℃	

【1】Exceeding any one or combination of these limits may cause permanent damage.

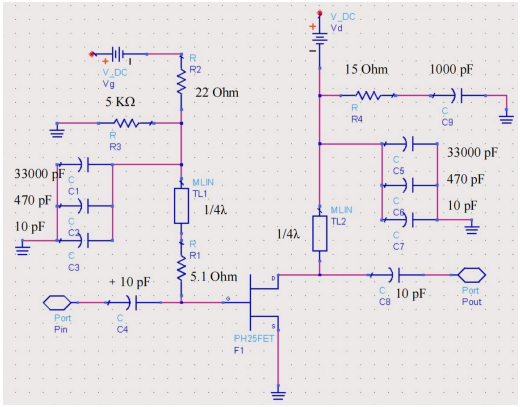
Outline Drawing



Dimension Symbols

Symbol	Value (unit: mm)	
	Min.	Max.
U1	23.80	24.20
U2	17.20	17.60
A	-	5.2

Application Circuit



Pad Definition

No	Function
1	Source
2	Vd
3	Vg

Note:

(1) The device is an internal matching device, and the input and output impedance values are both 50 ohms;

(2) Power-on sequence: first add negative electricity to the gate, and then add positive electricity to the drain.